November 1999

FAIRCHILD SEMICONDUCTOR

FDR8305N

Dual N-Channel 2.5V Specified PowerTrench® MOSFET

General Description

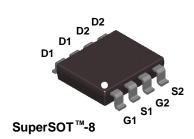
These N-Channel 2.5V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

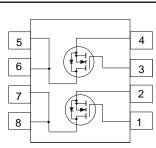
Applications

- Load switch
- Motor driving
- Power Management

Features

- 4.5 A, 20 V. $R_{DS(ON)} = 0.022 \ \Omega \ @ V_{GS} = 4.5 \ V$ $R_{DS(ON)} = 0.028 \ \Omega \ @ V_{GS} = 2.5 \ V.$
- Low gate charge (16.2nC typical).
- Fast switching speed.
- High performance trench technology for extremely low $R_{\mbox{\tiny DS(ON)}}.$
- Small footprint (38% smaller than a standard SO-8);low profile package (1 mm thick); power handling capability similar to SO-8.





Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		20	V
V _{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1a)	4.5	A
	- Pulsed		20	
PD	Power Dissipation for Single Operation	(Note 1a)	0.8	W
TJ, T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.8305	FDR8305N	13"	12mm	3000 units

Electrical Characteristics $T_{A} = 25^{\circ}C$ unless otherwise noted Symbol Parameter **Test Conditions** Min Max Units Typ **Off Characteristics** Drain-Source Breakdown Voltage 20 BV_{DSS} $V_{GS} = 0 V, I_D = 250 \mu A$ V Breakdown Voltage Temperature $I_D = 250 \ \mu A$, Referenced to 14 ΔBV DSS mV/°C Coefficient 25°C ΔT_{J} Zero Gate Voltage Drain Current $V_{DS} = 16 V, V_{GS} = 0 V$ 1 μA IDSS Gate-Body Leakage Current, $V_{GS} = 8 V, V_{DS} = 0 V$ 100 IGSSF nA Forward $V_{GS} = -8 V, V_{DS} = 0 V$ -100 Gate-Body Leakage Current, nA IGSSR Reverse On Characteristics (Note 2) V_{GS(th)} Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \ \mu A$ 0.4 0.85 1.5 v Gate Threshold Voltage $I_D = 250 \ \mu A$, Referenced to mV/°C -3 $\Delta V_{GS(th)}$ **Temperature Coefficient** 25°C $\Delta T_{\rm J}$ R_{DS(on)} Static Drain-Source $V_{GS} = 4.5 \text{ V}, I_D = 4.5 \text{ A}$ 0.015 0.022 Ω **On-Resistance** V_{GS}=4.5 V, I_D=4.5 A, T_J=125°C 0.026 0.040 0.020 0.028 $V_{GS} = 2.5 \text{ V}, I_D = 4 \text{ A}$ On-State Drain Current $V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$ 10 А I_{D(on)} Forward Transconductance V_{DS} = 4.5 V, I_D = 4.5 A 24 S **g**FS **Dynamic Characteristics** Ciss Input Capacitance $V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$ 1600 pF f = 1.0 MHz Coss Output Capacitance 380 pF Crss **Reverse Transfer Capacitance** 200 рF Switching Characteristics (Note 2) Turn-On Delay Time $V_{DD} = 10 V, I_D = 1 A,$ 22 12 t_{d(on)} ns V_{GS} = 4.5 V, R_{GEN} = 6 Ω tr Turn-On Rise Time 15 27 ns Turn-Off Delay Time 35 55 td(off) ns Turn-Off Fall Time tf 18 30 ns Qg **Total Gate Charge** $V_{DS} = 10 V, I_{D} = 4.5 A,$ 16.2 23 nC $V_{GS} = 4.5 V$ Q_{gs} Gate-Source Charge 2.5 nC Q_{gd} Gate-Drain Charge 5.5 nC **Drain-Source Diode Characteristics and Maximum Ratings** Maximum Continuous Drain-Source Diode Forward Current 0.67 Is А V_{SD} Drain-Source Diode Forward Voltage V_{GS} = 0 V, I_S = 0.67 A 0.65 1.2 V (Note Notes 1. R_{0.1A} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.

R_{0,C} is guaranteed by design while R_{0,CA} is determined by the user's board design. Both devices are assumed to be operating and sharing the dissipated heat energy equally.

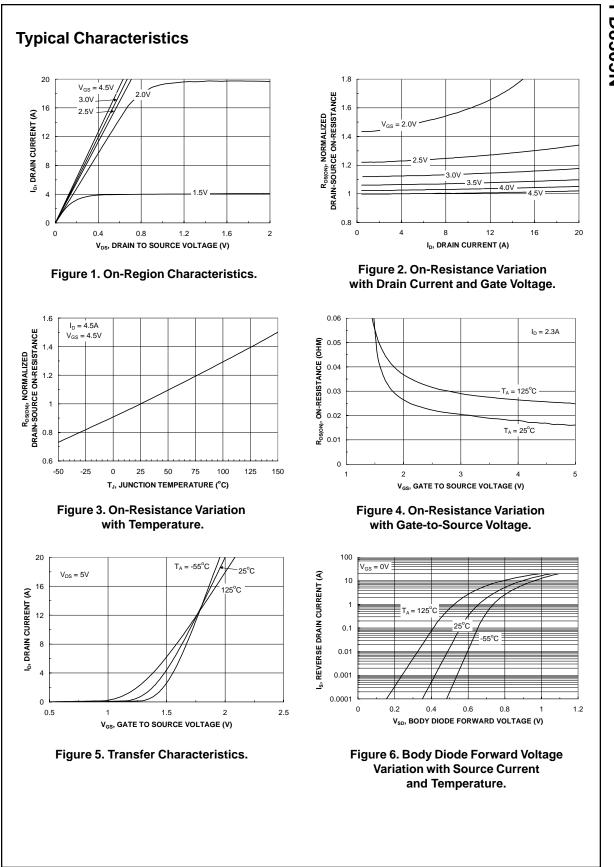
156°C/W on a minimum mountingpad of 2oz copper.

Scale 1:1 on letter size paper

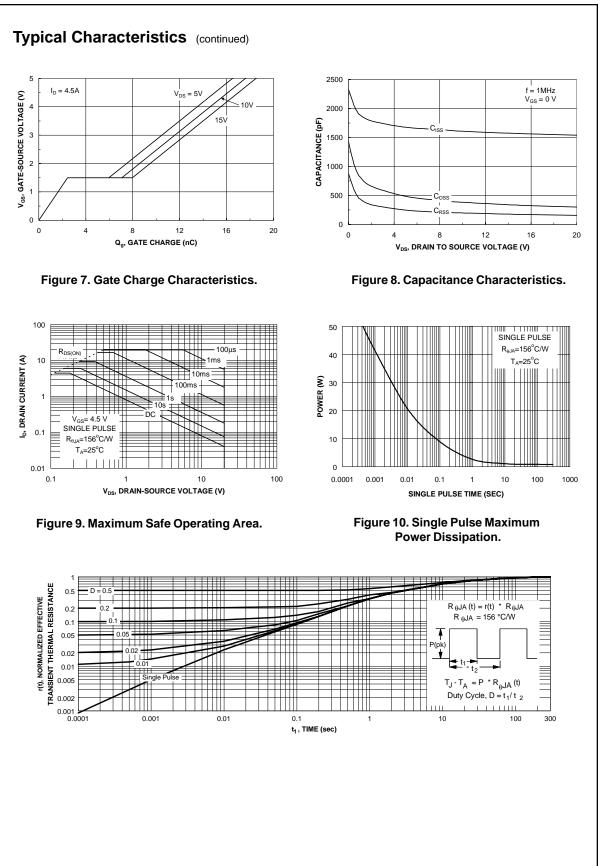
200

2. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%.

FD8305N

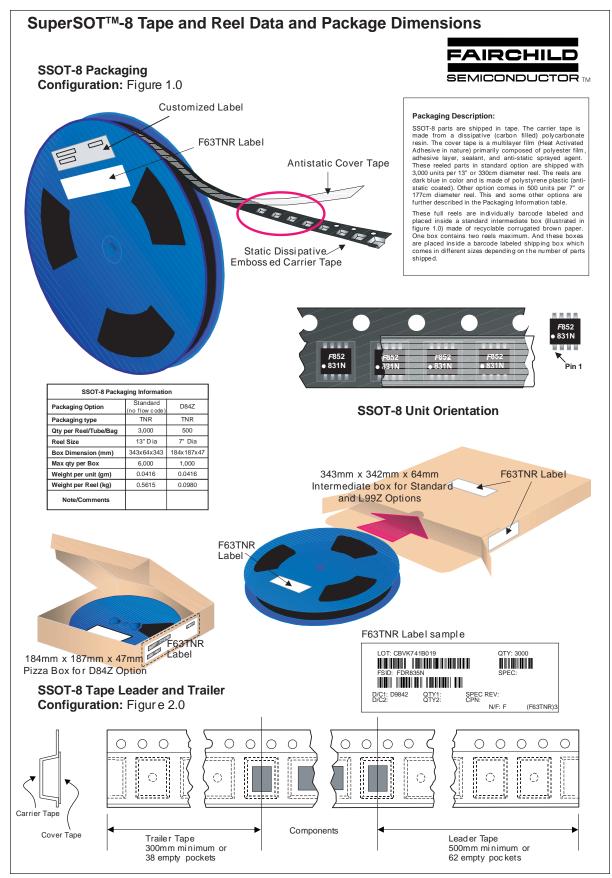


FD8305N

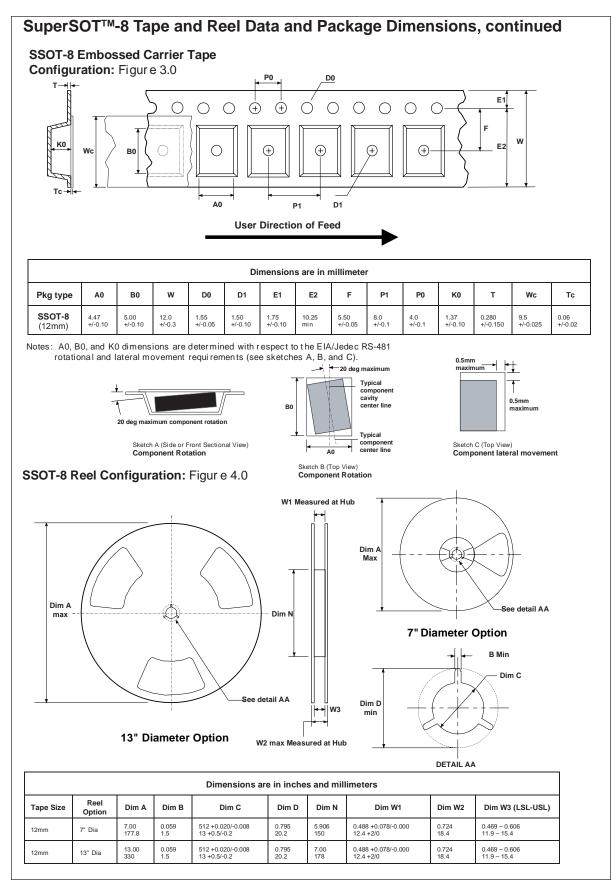


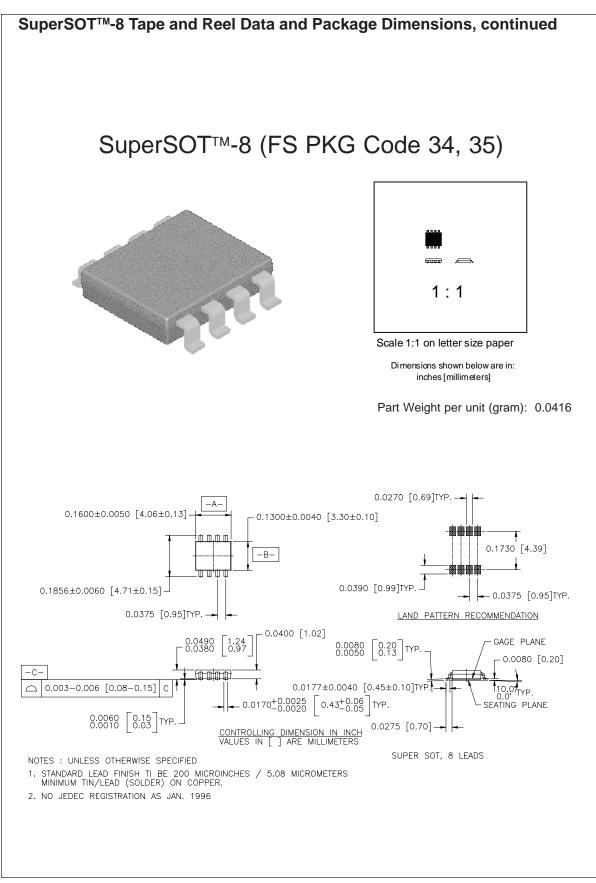
FD8305N Rev. C

FD8305N



August 1999, Rev. C





TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACExTM CoolFETTM CROSSVOLTTM E²CMOSTM FACTTM FACT Quiet SeriesTM FAST[®] FAST[®] FASTrTM GTOTM HiSeCTM ISOPLANAR™ MICROWIRE™ POP™ PowerTrench® QFET™ QS™ Quiet Series™ SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SyncFET™ TinyLogic™ UHC™ VCX™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user. 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.